

In the disclosure:

Please change the paragraph at page 1, line 21, as follows:

--As the following consideration shows, such a thin SiO_2 intermediate layer reduces the dielectric effectiveness of the substitute material. If we assume that the thickness $t_{\text{high-}k} t_{\text{high-}k}$ of the alternative dielectric is to afford the same capacitance as an SiO_2 layer of the equivalent thickness t_{eq} , that gives:

$$t_{\text{high-}k} = (k_{\text{high-}k} / k_{\text{SiO}_2}) t_{\text{eq}}, \quad t_{\text{high-}k} = (k_{\text{high-}k} / k_{\text{SiO}_2}) t_{\text{eq}}, \quad (1)$$

wherein k_{SiO_2} is the dielectric constant of the SiO_2 . As the SiO_2 intermediate layer represents a second capacitance C_{SiO_2} connected in series with the alternative dielectric, the resulting capacitance can be calculated as follow:

$$1/C_{\text{res}} = 1/C_{\text{high-}k} + 1/C_{\text{SiO}_2}, \quad (2)$$

wherein $C_{\text{high-}k}$ is the capacitance of the dielectric layer. Using (1), that then gives the following for the equivalent thickness of the layer system t_{eq} , comprising a thin SiO_2 layer t_{SiO_2} and the dielectric layer $t_{\text{high-}k}$,

$$t_{\text{eq}}^s = t_{\text{SiO}_2} + (k_{\text{SiO}_2} / k_{\text{high-}k}) t_{\text{high-}k}, \quad t_{\text{high-}k}. \quad (3) --$$